## SIR for TELIS (post-critical review)

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### List of participants

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## SIR for TELIS (post-critical review)

#### • Four Technical Notes, distributed after April 2004

- 1. FFO power and linewidth (dependence on design and FFO parameters)
- 2. Optimization of the HM and PLL operation
- 3. Results of preliminary tests of T2 SIRs and mixer cryostat electronics (including TMM)
- 4. Numerical simulation of an SIS mixer output spectrum. Dependency of an SIR resolution and dynamic range on autonomous FFO LW
- <u>Considerable improvement of the IREE technology</u> (SIR yield for batch T2m-031 > 90 %)
- First T2m devices were tested as a receiver with PL Uncorrected receiver DSB noise temperature is of about 500 K at 600 GHz and 630 K at 680 GHz

#### IVCs of the FFO of HD 11 design, measured at different magnetic fields



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# Dependence of the HM current (HM pumping) induced by FFO (HD-11) on the FFO frequency



## HM pumping and Spectral Ratio of the PL FFO as a function of FFO bias current.

#### FFO frequency 670 GHz



# FFO linewidth and Spectral Ratio PL FFO on its oscillation frequency.



# Linewidth of free-running FFOs and SR for the PL FFO as a function of FFO width.



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#### SR of the PL FFO with increased overlapping All circuits are from the same batch, Jc= 7 kA/cm<sup>2</sup>





### Spectral ratio of the PL FFO vs IF level output of the PLL system



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# Spectral Ratio of the PL FFO vs free running FFO linewidth



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#### Spectra of the phase-locked and frequency locked FFO + reconstructed PL spectra



#### **Computer- simulated spectrum of HCI line**



# The form of the output spectra at conversion of the HCI line for phase locked FFO



### **Relative error of conversion of the HCI line**



### **Spectral Ratio vs FFO LW for different PLLBW**



PLL BW is limited by length of the cables.

Cryogenic PLL is required!

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### **T2m SIR Microcircuit for TELIS**



4 x 4 x 0. 5 mm<sup>3</sup> (Si) Nb-AlOx-Nb Jc = 8 kA/cm<sup>2</sup> Optionally: SIS - Jc = 8 kA/cm<sup>2</sup> FFO + HM = 5 kA/cm<sup>2</sup>

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### **T2m SIR Microcircuit for TELIS**



SIS and HM pumping & FTS response for T2m



### **SIS pumping for different T2m FFO designs**



# Normalized SIS and HM pumping – T2m, DDA $(I_g SIS = 100 \ \mu A, I_g HM = 172 \ \mu A)$



#### **FTS data for double-dipole twin SIS mixer.** A dip at 560 GHz corresponds to water line.



Hot - Cold response for DSA-TM (T2m-031#20c)



#### Pumped IVC and Y Factor for T2m-031#20c



# FFO linewidth vs FFO frequency, measured at different temperatures



#### Spectral Ratio of the PL FFO vs frequency, measured at different temperatures



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### **Conclusion (FFO issue)**

- Essential dependencies of the FFO linewidth on its frequency, current density and geometry was found;
- Improved design of the FFO for TELIS has been developed and optimized;
- Free-running linewidth from 9 to 2 MHz recorded in the frequency range 500 – 710 GHz (Spectral Ratio of the PL FFO varies from 35 to 87 % correspondingly);
- Free-running linewidth of the FFO below 1 MHz is required to obtain good Spectral Ratio and measure the complicated line profiles with error below 1% (2.5 MHz is the upper limit for 10% error);
- Ultra-wideband cryogenic PLL is needed to realize an ultimate performance of the integrated FFO.

### **Conclusion (SIR issue)**

- Concepts of PL SIR are developed and tested.
- Second generation of the PL SIR IC for TELIS has been developed showing a possibility to realize TELIS requirements.
- Uncorrected receiver DSB noise temperature is of about 500 K at 600 GHz and 630 K at 680 GHz
- Procedure for remote optimization of the PL SIR operation has been developed and experimentally proven.

## List of problems and worries (1)

- 1. Troubles and worries that considerably slow-down the SIR\_TELIS measurement and did not allow yet to come to real problems:
- 1a. Absence of the low-noise computer controlled FFO bias supply;
- 1b. Limited (almost to zero level) support of electronic and mechanical workshops;
- 1c. Shortage of Liquid Helium;
- 1d. Delay in TMM production;
- 1e. Absence of the licensed software for microwave design and analysis at IREE;
- 1f. Limited information on scientific requirements of TELIS program (requirements on the LO line shape; most interesting frequencies for TELIS operation).

## List of problems and worries (2)

#### 2. Already accounted SIR\_TELIS problems:

**2a.** System complexity problem (N<sup> $\alpha$ </sup> problem;  $\alpha$  > 2);

- 2b. Not sufficient cooling of the chip (FFO leakage current);
- 2c. Direct detection of the Hot/Cold load by FFO;
- 2d. Influence of the synthesizer power on the SIS-mixer;
- 2e. TMM design (SIS IF output performance);
- 2f. SIR chip design:
  - Input Bandwidth (FTS) flatness
    - Range of the FFO/SIS pumping f > 620 GHz
    - Superfine resonance structure
    - Low Signal to Noise Ratio for HM

## List of proposed actions (3) :

3a. (Complexity problem) – Recognition and realization of the task complexity;

3b. (Cooling of the chip) – Joint action: determination of the reasons, additional filters, improved contact of the lens to mixer block, additional cooling straps to chip;

3c. (Direct detection) – Input Band Pass Filters; PLL stabilization of the FFO;

3d. (Influence of Synthesizer on SIS) – Decrease of the HM area down to 1  $\mu$ m<sup>2</sup>, optimization of the TMM design and bonding (ribbon bonding);

3e. (TMM design – IF performance) – Test of originally designed and modified TMM; new TMM design.

3f. (SIR chip design) - Next generations of the SIR chip: modeling, design and test

- T3 design 12/2004; fabrication 02/2005; test 05/2005;
- T4 design 07/2004; fabrication 10/2005; test 12/2005;
- T5 design 06/2006; fabrication 09/2006; test 12/2006;